

# Supplemental Material for “Rapid optimal work extraction from a quantum-dot information engine”

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## A. DEVICE FABRICATION

The devices were processed in the Institute of Science and Technology Austria Nanofabrication facility. A 6x6 mm<sup>2</sup> chip comprising of Ge quantum well sandwiched between Si<sub>0.3</sub>Ge<sub>0.7</sub> is cleaned before further processing. Further details about the quantum well growth can be found in Ref. [1]. First, ohmic contacts are patterned in a 100 keV electron beam lithography system. Subsequently, a few nanometers of native oxide is milled by argon bombardment which is followed by deposition of 60 nm Pt layer. A 20 nm thick layer of aluminium oxide is deposited at 300°C in an atomic layer deposition step, followed by gates consisting of 3 nm Ti and 27 nm Pd.

## B. CHARACTERISATION OF THE TUNNEL RATES AND LEVER ARM

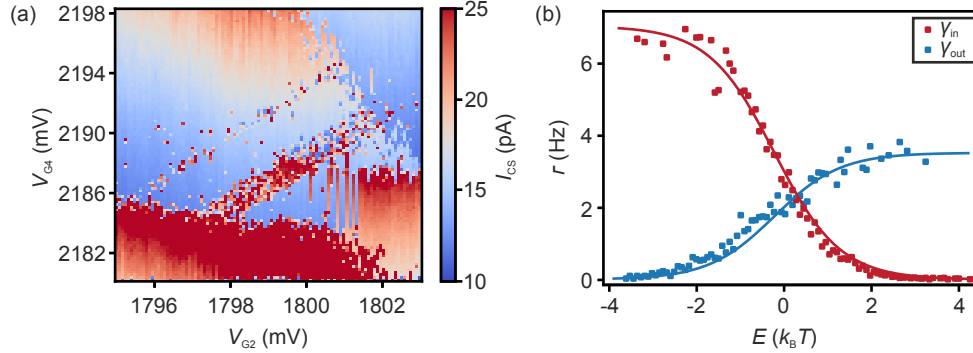


FIG. B1. (a) A set of bias triangles measured by varying  $V_{G2}$  and  $V_{G4}$  and recording the current  $I_{CS}$  through the charge sensor at a bias voltage  $V_{b,QD} = 0.32$  mV. (b) Tunneling rates  $\gamma_{in}$  and  $\gamma_{out}$  of QD1.

The measurements were performed in a dilution refrigerator at a base temperature of 150 mK. The charge sensor and the double quantum dot are isolated by creating an electrostatic barrier using splitter gate voltages  $V_{S1-S2}$ . The double quantum dot in the bottom array is tuned by using the gates voltages  $V_{G2}$  and  $V_{G4}$ . The tunneling between Fermi reservoirs and double quantum dot is controlled using gate voltages  $V_{G1}$  and  $V_{G5}$ . The inter-dot tunneling is set by the gate voltage  $V_{G3}$ . Similarly, the charge sensor is tuned by a combination of gate voltages  $V_{CS1-CS3}$ . We

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first measure a set of bias triangles, as shown in Fig. B1(a), at a fixed bias  $V_{b, \text{QD}} = 0.32$  mV. We extract a lever arm  $\alpha = \frac{V_{b, \text{QD}}}{\Delta V_{G2}} = 0.041 \pm 0.002$ . Time traces across the transition from  $n = 0$  to  $n = 1$  were recorded. Tunnel rates and electron temperature were extracted in Fig. B1(b) using the functions:  $\gamma_{\text{in}} = \Gamma_{\text{in}} f(E)$  and  $\gamma_{\text{out}} = \Gamma_{\text{out}} (1 - f(E))$ , where  $f(E) = (1 + e^{E/k_B T})^{-1}$ , which describe the tunneling in and out rates of the quantum dot [2]. We obtain an electron temperature of  $T = 180$  mK from these fits.

### C. CALIBRATION DRIFT

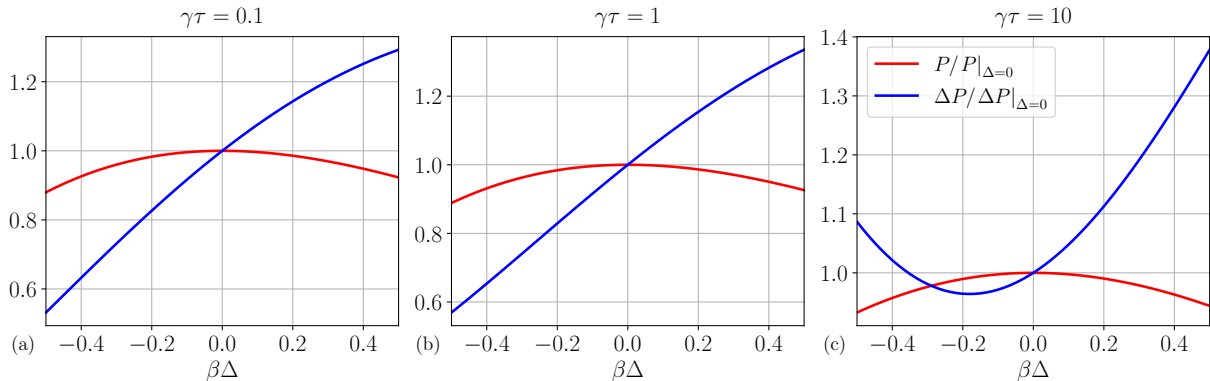


FIG. C2. Relative change of power and fluctuations for a constant shift from the optimal protocol  $\varepsilon(t) \rightarrow \varepsilon(t) + \Delta$  for all the regimes of driving speeds: (a)  $\gamma\tau = 0.1$ , (b)  $\gamma\tau = 1$ , (c)  $\gamma\tau = 10$ .

Since the calibration drift takes much longer than the duration of a single cycle (even in the slow driving regime) we can assume that within a cycle it corresponds to a constant shift of the energy  $\varepsilon \rightarrow \varepsilon + \Delta$ . In Fig. C2 we show how this shift affects the power and fluctuations relative to their value in absence of the shift. As expected, since the power is optimal for  $\Delta = 0$ , we see that for small shifts it deviates from its optimal value as  $\mathcal{O}(\Delta^2)$ . Conversely, it is clear that this is not the case for  $\Delta P$  since the protocols do not optimise the fluctuations. Therefore its deviations scale as  $\mathcal{O}(\Delta)$ . This makes the fluctuations more sensitive than the power to this shift caused by the calibration drift.

### D. MEASUREMENT STATISTICS

In this section we present how to compute the estimators – and their variance – for expected work and work fluctuations that were used for the plotted values and error bars in Fig. 2. For  $N$  i.i.d statistical samples  $\{W_i\}_{i=1}^N$  of a random variable  $\mathcal{W}$ . We estimate the expected value of  $\mathcal{W}$  with the mean:

$$E(\{W_i\}_{i=1}^N) := \frac{1}{N} \sum_{i=1}^N W_i. \quad (\text{D1})$$

It is straightforward to compute the expected value and variance of this estimator:

$$\langle E(\{W_i\}_{i=1}^N) \rangle = \langle \mathcal{W} \rangle, \quad (\text{D2})$$

$$\text{Var}(E(\{W_i\}_{i=1}^N)) = \frac{\text{Var}(\mathcal{W})}{N}. \quad (\text{D3})$$

Therefore, with  $N$  samples of work gain  $\{W_i\}_{i=1}^N$ , we compute the expected work with the estimator  $E$  and use the square root of its variance for its error in the plots. To compute the variance from the sample, we use the following estimator

$$V(\{W_i\}_{i=1}^N) = \frac{1}{N-1} \sum_{i=1}^N (W_i - E(\{W_i\}_{i=1}^N))^2, \quad (\text{D4})$$

which we can use also to estimate the fluctuations of the work gain. The expected value and variance of this estimator give

$$\langle V(\{W_i\}_{i=1}^N) \rangle = \text{Var}(\mathcal{W}) , \quad (\text{D5})$$

$$\text{Var}(V(\{W_i\}_{i=1}^N)) = \langle \mathcal{W}^4 \rangle \frac{N(N-4)+1}{N(N-1)^2} - \frac{4\langle \mathcal{W}^3 \rangle \langle \mathcal{W} \rangle}{N} - \frac{\text{Var}(\mathcal{W})^2}{N-1} + \frac{3\langle \mathcal{W}^2 \rangle^2}{N} , \quad (\text{D6})$$

where we can use the maximum likelihood estimators for the 2nd, 3rd and 4th moments –  $m_2$ ,  $m_3$  and  $m_4$  respectively – to compute the error of the estimator of the work fluctuations from the statistical samples. These maximum likelihood estimators are given by

$$m_j(\{W_i\}_{i=1}^N) := \frac{1}{N} \sum_i W_i^j , \quad (\text{D7})$$

and satisfy  $\langle m_j(\{W_i\}_{i=1}^N) \rangle = \langle \mathcal{W}^j \rangle$ .

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- [2] A. Hofmann, V. F. Maisi, C. Rössler, J. Basset, T. Krähenmann, P. Märki, T. Ihn, K. Ensslin, C. Reichl, and W. Wegscheider, [Phys. Rev. B](#) **93**, 035425 (2016).